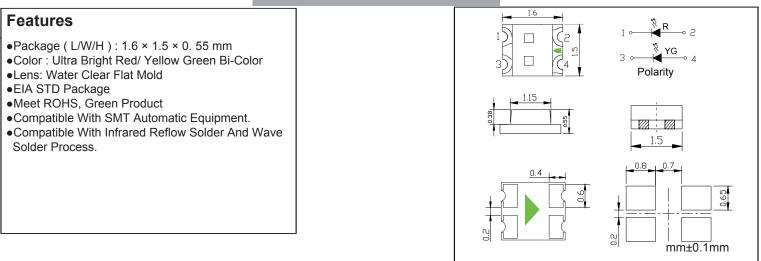


## 0603红/普绿双色

## **Light Emitting Diode**



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating		Unit		
Power Dissipation	Pd	R	60	mW		
		YG	60			
Peak Forward Current	IFP	R	50	mA		
(1/10 Duty Cycle, 0.1ms Pulse Width)	IFP	YG	50			
DC Forward Current	IF	R	25	mA		
		YG	25	IIIA		
Reverse Voltage	VR	R	5	v		
		YG	5			
Operating Temperature Range	Topr	$-30^{\circ}C \sim +85^{\circ}C$				
Storage Temperature Range	Tstg	$-40^{\circ}C  \sim  +90^{\circ}C$				
Soldering Condition	Tsol	Reflow soldering : 255 °C For 5 Seconds Hand soldering: 300 °C For 3 Seconds				

## Electrical Specification (TA=25°C unless otherwise specified)

Parameter	Symbol	Color	Min.	Тур.	Max.	Unit	Test Condition
Luminous Intensity	IV	R	80		130	mcd	IF = 20mA
		YG	30		55		
Dominant Wavelength	λd	R	620		630	nm	IF=20mA
		YG	568		578		
Peak Wavelength	λp	R		630		nm	IF=20mA
		YG		570			
Spectral Line Half-Width	Δλ	R		20		nm	IF=20mA
		YG		15			
Forward Voltage	VF	R	1.8		2.4	V	IF=20mA
		YG	1.8		2.4		
Reverse Current	IR	R			10	uA	VR=5V
		YG			10		
Viewing Angle	201/2			120		deg	IF = 20mA

Notes: 1. Luminous intensity is measured with a light sensor and filter combination that approximates the CIE eye-response curve.

2.  $\theta 1/2$  is the off-axis angle at which the luminous intensity is half the axial luminous intensity.

3. The dominant wavelength,  $\lambda d$  is derived from the CIE chromaticity diagram and represents the

single wavelength which defines the color of the device.



